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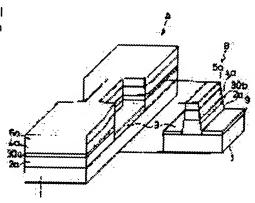
(72)Inventor: MURAKAMI TAKASHI

GOTO KATSUHIKO

(54) SEMICONDUCTOR OPTICAL DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PURPOSE: To obtain a semiconductor laser having an active layer, in which the laser outgoing end-face side is thinned and the inside of a laser is formed in thick layer thickness, on a flat surface having no stepped section and manufacture thereof. CONSTITUTION: Two striped SiO2 films 9 are formed in parallel while mutually forming a regular interval in a region positioned in a laser resonator shaped onto a GaAs substrate 1 on the GaAs substrate 1, and AlGaAs clad layers 2a are formed through an organometallic vapor growth method in an atomic—layer epitaxial mode. AlGaAs active layers 30a and 30b (the inside of a laser) are shaped through the organometallic vapor growth method in a normal mode, and AlGaAs clad layers 4a and GaAs clad layers 5a are formed through the organometallic vapor growth method in the atomic—layer epitaxial mode.



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